



# **MURANG'A UNIVERSITY OF TECHNOLOGY**

## **SCHOOL OF ENGINEERING AND TECHNOLOGY**

DEPARTMENT OF ELECTRICAL AND ELECTRONICS ENGINEERING

UNIVERSITY ORDINARY EXAMINATION

2023/2024 ACADEMIC YEAR

**SECOND YEAR SECOND SEMESTER EXAMINATION FOR BACHELOR  
OF SCIENCE IN ELECTRICAL AND ELECTRONICS ENGINEERING**

**EET201: ANALOGUE ELECTRONICS**

**DURATION: 2 HOURS**

### **INSTRUCTIONS TO CANDIDATES:**

1. Answer Question one and any other two questions.
2. Mobile phones are not allowed in the examination room.
3. You are not allowed to write on this examination question paper.

## SECTION A: ANSWER ALL QUESTIONS IN THIS SECTION

### QUESTION ONE (30 MARKS)

- a) A certain P-N junction diode has a leakage current of  $10^{-14}$  A at room temperature of  $27^{\circ}\text{C}$  and  $10^{-9}$  A at  $125^{\circ}\text{C}$ . The diode is forward biased with a constant – current source of 1mA at room temperature. If current is assumed to remain constant, calculate the junction barrier voltage at room temperature and at  $125^{\circ}\text{C}$  (5marks)
- b) For the circuit in Fig. 1(b) find;
- $I_B$
  - $I_e$
  - $I_E$
  - $V_{CC}$ , neglect  $V_{BE}$  (5marks)
- c) Using well-labelled diagram, explain the theory of operation of a depletion mode of N. channel MOSFET (5marks)
- d) An amplifier having a gain of 500 without feedback has an overall negative feedback applied which reduces the gain to 100. Calculate the fraction of output voltage feedback. If due to ageing of components, the gain without feedback falls by 20%, calculate the percentage fall in gain without feedback (5marks)
- e) Calculate the oscillator frequency for a FET Hartley oscillator (refer to fig 1(e) for the following circuit values;  $C=250\text{pF}$ ;  $L_1 = 1.5\text{mH}$ ,  $L_2=1.5\text{mH}$ , and  $m=0.5\text{mH}$  (5marks)
- f) Explain theory of operation of a complementary symmetry push-pull, class B Amplifier providing a well-labelled circuit diagram (5marks)

## SECTION TWO: ANSWER ANY TWO QUESTIONS

### QUESTION TWO (20 MARKS)

- a) A half-wave rectifier using silicon diode has a secondary emf of 14.14v(rms) with a resistance of  $0.2\Omega$ . The diode has a forward resistance of  $0.05\Omega$  and a forward voltage of 0.7v. If load resistance is  $10\Omega$ , determine
- Dc load current

- ii. Dc load voltage
  - iii. Voltage regulation
  - iv. Efficiency (8marks)
- b) Using well- labelled diagrams and waveforms, explain how a 3-phase full wave rectifier works. (6marks)
- c) Find the exact expression of Emitter current in terms of the parameters indicated in the diagram, for the two-supply \_\_\_\_\_ bias circuit of fig 2( c ) (6marks)

**QUESTION THREE (20 MARKS)**

- a) For a N-channel JFET,  $I_{DSS} = 7.7\text{mA}$ ,  $V_P = 3\text{V}$ ,  $V_{GS} = -1\text{V}$  find the value of;
- i)  $I_D$
  - ii)  $G_{mo}$
  - iii)  $G_m$  (6marks)
- b) For the colpitts oscillator circuit shown in Fig.3(b) find the values of;
- i. Feedback fraction
  - ii. Minimum gain to sustain osc \_\_\_\_\_
  - iii. Emitter resistor  $R_E$  (6marks)
- c) For the two –stage RC-coupled low-level audio \_\_\_\_\_ shown in fig.3( c ) compute the following
- i.  $V_i$
  - ii.  $A_{v1}$
  - iii.  $A_{v2}$
  - iv.  $A_v$  in dB neglect  $V_{BE}$  and take  $V_e = 25\text{mV}/I_E$

**QUESTION FOUR (20 MARKS)**

- a) The signal input to a small signal amplifier consists of 50uW of signal power and 0.5uW of noise power. The amplifier generates an internal noise power of 50uW and has a gain of 20dB. For this \_\_\_\_\_ compute;
- i. Input S/N
  - ii. Output S/N
  - iii. Noise factor

- iv. Noise figure (7marks)
- b) For the Rc-coupled circuit of fig. 4(b), calculate the lower cut-off frequency
  - i. At  $C_1$
  - ii. At  $C_2$
  - iii. For the amplifier (6marks)
- c) Using a well labelled diagram, Explain how analog electronics are applied in FM Transmitter system. (7marks)